

medium capable of maintaining an electric field with no supply of energy from outside source.--

Page 38, replace the paragraph beginning on line 21, bridging page 39, as follows:

--An inter-layer insulator 28 of silicon dioxide entirely overlies the substrate, so that the hetero-junction bipolar transistor 100, the resistive element 200 and the metal-insulator-metal capacitor 300 are buried in the inter-layer insulator 28. The emitter electrode 20, the base electrode 21, and the collector electrode 22, and the resistive element electrodes 26 as well as the top electrode 27 are electrically connected through contact electrode contacts to second level interconnections 29. The contact electrode contacts are provided in contact holes formed in the inter-layer insulator 28. The second level interconnections 29 extend over the inter-layer insulator 28. The inter-layer insulator 28 has a planarized top surface.--

IN THE CLAIMS:

Amend claim 1 as follows:

B' --1. (amended) A monolithically integrated semiconductor device comprising:

B1
level
a hetero-junction bipolar transistor having at least one electrode contact layer which contacts directly with at least one of collector, base and emitter electrodes; and

at least one passive device having at least one passive device electrode having two resistive elemental electrode contacts and at least one resistive element layer, contacting said two resistive element electrode contacts,

wherein said electrode contact layer and said resistive element layer comprise the same compound semiconductor layer.--

[Amend claim 3 as follows:]

B2
--3. (amended) The device as claimed in claim 1, wherein said at least one passive device further comprises a metal-insulator-metal capacitor which comprises a bottom electrode, a capacitive dielectric layer and a top electrode.--

Cancel claims 19-41.

Amend claim 42 as follows:

--42. (amended) A monolithically integrated semiconductor device comprising:

B3
a hetero-junction bipolar transistor having at least one electrode contact layer which contacts directly with at least one of collector, base and emitter electrodes; and

B3
level
at least one passive device comprising a metal-insulator-metal capacitor having a bottom electrode, a capacitive dielectric layer and a top electrode,

wherein one of said bottom and top electrodes and one of said collector, base and emitter electrodes comprise the same metal layer and have a same thickness.--

Cancel claims 43 and 44.

Amend claim 45 as follows:

--45. (amended) The device as claimed in claim 42, wherein said at least passive device further comprises:

B4
a resistive element which comprises: at least a resistive element layer; and at least a resistive element electrode.--

Cancel claim 46.

Amend claim 47 as follows:

--47. (amended) A monolithically integrated semiconductor device comprising:

JS
a hetero-junction bipolar transistor having at least one electrode contact layer which contacts directly with at least one of collector, base and emitter electrodes;

a resistive element which comprises at least a resistive element layer, and at least one resistive element electrode; and

BS
wml
a metal-insulator-metal capacitor which comprises a bottom electrode, a capacitive dielectric layer, and a top electrode,

wherein said electrode contact layer, said resistive element layer and said capacitive dielectric layer comprise the same compound semiconductor layer, and

wherein said resistive element electrode, said top electrode and said at least one of collector, base and emitter electrodes comprises the same metal layer having a same thickness.--

Cancel claim 52.

Add the following new claim:

--53. (new) A monolithic integrated semiconductor device comprising:

B6
a hetero-junction bipolar transistor having at least one electrode contact layer that directly contacts with at least one of collector, base and emitter electrodes;

at least one passive device having at least one passive device electrode and at least one resistive layer